

IEEE Xplore search for paper no. 0705


[Home](#) | [Login](#) | [Logout](#) | [Access Information](#) | [Alerts](#) |

Welcome United States Patent and Trademark Office

Search Results

[BROWSE](#)[SEARCH](#)[IEEE XPLORE GUIDE](#)

Results for "( trapping&lt;in&gt;metadata ) &lt;and&gt; ( plasma&lt;in&gt;metadata ) &lt;and&gt; ( implantation&amp;..."



Your search matched 21 of 1193303 documents.

A maximum of 100 results are displayed, 25 to a page, sorted by Relevance in Descending order.

[» View Session History](#)[» New Search](#)[» Key](#)

IEEE JNL IEEE Journal or Magazine

IEE JNL IEE Journal or Magazine

IEEE CNF IEEE Conference Proceeding

IEE CNF IEE Conference Proceeding

IEEE STD IEEE Standard

Modify Search

( trapping&lt;in&gt;metadata ) &lt;and&gt; ( plasma&lt;in&gt;metadata ) &lt;and&gt; ( implantation&lt;in&gt;me

☐ Check to search only within this results setDisplay Format: ☒ Citation ☐ Citation & Abstract

Select Article Information

- ☐ 1. **Transfer of single crystalline silicon nanolayer onto alien substrate**  
Usenko, A.Y.; Carr, W.N.; Bo Chen; Nanotechnology, IEEE Transactions on Volume 3, Issue 2, June 2004 Page(s):225 - 229  
[AbstractPlus](#) | [References](#) | Full Text: [PDF](#)(488 KB) IEEE JNL
- ☐ 2. **The effects of fluorine passivation on polysilicon thin-film transistors**  
Horng Nan Chern; Chung Len Lee; Tan Fu Lei; Electron Devices, IEEE Transactions on Volume 41, Issue 5, May 1994 Page(s):698 - 702  
[AbstractPlus](#) | Full Text: [PDF](#)(416 KB) IEEE JNL
- ☐ 3. **Antioxidant and its reaction products as charge trapping centres in crosslinked**  
Teyssedre, G.; Laurent, C.; Campus, A.; Nilsson, U.H.; Montanari, G.C.; Electrical Insulation and Dielectric Phenomena, 2003. Annual Report. Conference on 2003 Page(s):96 - 99  
[AbstractPlus](#) | Full Text: [PDF](#)(347 KB) IEEE CNF
- ☐ 4. **Preliminary assessment of the tritium inventory and permeation in the plasma facing components of ITER**  
Federici, G.; Holland, D.; Brooks, J.; Causey, R.; Dolan, T.J.; Longhurst, G.; Fusion Engineering, 1995. SOFE '95. 'Seeking a New Energy Era', 16th IEEE/NPSS S Volume 1, 30 Sept.-5 Oct. 1995 Page(s):418 - 423 vol.1  
[AbstractPlus](#) | Full Text: [PDF](#)(632 KB) IEEE CNF
- ☐ 5. **A novel method to suppress transient enhanced diffusion of low energy implants on reactive plasma etching**  
Privitera, V.; Priolo, F.; Mannino, G.; Napolitani, E.; Carnera, A.; Ion Implantation Technology Proceedings, 1998 International Conference on Volume 2, 22-26 June 1998 Page(s):845 - 848 vol.2  
[AbstractPlus](#) | Full Text: [PDF](#)(424 KB) IEEE CNF
- ☐ 6. **Comparison of charge control technologies for advanced high current ion implantation**  
Erokhin, Y.; Sawyer, W.; Mack, M.E.; Santiesteban, R.; Mason, P.; Persson, E.; Treible Ion Implantation Technology Proceedings, 1998 International Conference on Volume 1, 22-26 June 1998 Page(s):436 - 439 vol.1  
[AbstractPlus](#) | Full Text: [PDF](#)(352 KB) IEEE CNF

- ☐ 7. **Electrical characterization of ultra-shallow junctions formed by plasma immersion**  
Yang, B.L.; Wong, H.; Han, P.G.; Poon, M.C.;  
Microelectronics, 2000. Proceedings. 2000 22nd International Conference on  
Volume 2, 14-17 May 2000 Page(s):429 - 432 vol.2  
[AbstractPlus](#) | Full Text: [PDF](#)(132 KB) IEEE CNF
- ☐ 8. **Alternative Smart-cut-like process for ultra-thin SOI fabrication**  
Usenko, A.; Carr, W.N.; Bo Chen; Chabal, Y.;  
Advanced Semiconductor Manufacturing 2002 IEEE/SEMI Conference and Workshop  
30 April-2 May 2002 Page(s):6 - 10  
[AbstractPlus](#) | Full Text: [PDF](#)(460 KB) IEEE CNF
- ☐ 9. **Hydrogenation of polycrystalline silicon thin film transistors by plasma ion implantation**  
Bernstein, J.D.; Shu Qin; Chung Chan; Tsu-Jae King;  
Electron Device Letters, IEEE  
Volume 16, Issue 10, Oct. 1995 Page(s):421 - 423  
[AbstractPlus](#) | Full Text: [PDF](#)(264 KB) IEEE JNL
- ☐ 10. **Plasma damage immunity of thin gate oxide grown on very lightly N<sup>+</sup> implanted**  
Cheung, K.P.; Misra, D.; Colonell, J.I.; Liu, C.T.; Ma, Y.; Chang, C.P.; Lai, W.Y.C.; Liu,  
Electron Device Letters, IEEE  
Volume 19, Issue 7, July 1998 Page(s):231 - 233  
[AbstractPlus](#) | [References](#) | Full Text: [PDF](#)(64 KB) IEEE JNL
- ☐ 11. **Electron trap states and low frequency noise in tunnel junctions**  
Rogers, C.; Buhrman, R.; Gallagher, W.; Raider, S.; Kleinsasser, A.; Sandstrom, R.;  
Magnetics, IEEE Transactions on  
Volume 23, Issue 2, Mar 1987 Page(s):1658 - 1661  
[AbstractPlus](#) | Full Text: [PDF](#)(440 KB) IEEE JNL
- ☐ 12. **He self-pumping by tokamak pump limiter materials: Al, V, Ni, and Ni/Al alloys**  
Outten, C.A.; Barbour, J.C.; Doyle, B.L.; Walsh, D.S.;  
Fusion Engineering, 1991. Proceedings., 14th IEEE/NPSS Symposium on  
30 Sept.-3 Oct. 1991 Page(s):28 - 30 vol.1  
[AbstractPlus](#) | Full Text: [PDF](#)(184 KB) IEEE CNF
- ☐ 13. **Effects of mixing low-Z gases on a 2.45-GHz multiply charged ion source**  
Kato, Y.; Saitoh, M.; Kubo, Y.; Ishii, S.;  
Ion Implantation Technology. Proceedings of the 11th International Conference on  
16-21 June 1996 Page(s):418 - 421  
[AbstractPlus](#) | Full Text: [PDF](#)(316 KB) IEEE CNF
- ☐ 14. **Ultra-shallow junction formation using very low energy B and BF<sub>2</sub> sources**  
Osburn, C.M.; Downey, D.F.; Felch, S.B.; Lee, B.S.;  
Ion Implantation Technology. Proceedings of the 11th International Conference on  
16-21 June 1996 Page(s):607 - 610  
[AbstractPlus](#) | Full Text: [PDF](#)(464 KB) IEEE CNF
- ☐ 15. **Multicharged boron ions from pure elements evaporated in a 2.45-GHz ECR source**  
Kato, Y.; Fukukawa, A.; Ishii, S.;  
Ion Implantation Technology. Proceedings of the 11th International Conference on  
16-21 June 1996 Page(s):338 - 341  
[AbstractPlus](#) | Full Text: [PDF](#)(316 KB) IEEE CNF
- ☐ 16. **Particle transport reduction in a serial high current implanter**

Walther, S.R.; Sieradzki, M.; White, N.R.;  
Ion Implantation Technology. Proceedings of the 11th International Conference on  
16-21 June 1996 Page(s):170 - 173

[AbstractPlus](#) | Full Text: [PDF\(308 KB\)](#) IEEE CNF

- ☐ **17. Hydrogen in silicon: defect interactions and applications**  
Ashok, S.;  
Solid-State and Integrated Circuit Technology, 1998. Proceedings. 1998 5th International Conference on  
21-23 Oct. 1998 Page(s):749 - 752  
[AbstractPlus](#) | Full Text: [PDF\(212 KB\)](#) IEEE CNF
  
- ☐ **18. Metal ion discharge in crossed fields and its applications**  
Churkin, I.N.; Volosov, V.I.; Steshov, A.G.;  
Plasma Science, 1998. 25th Anniversary. IEEE Conference Record - Abstracts. 1998 International Conference on  
1-4 June 1998 Page(s):250  
[AbstractPlus](#) | Full Text: [PDF\(104 KB\)](#) IEEE CNF
  
- ☐ **19. Production of multiply charged ions by utilizing pulsed ECR plasma**  
Kato, Y.; Ishii, S.;  
Ion Implantation Technology Proceedings, 1998 International Conference on  
Volume 1, 22-26 June 1998 Page(s):448 - 451 vol.1  
[AbstractPlus](#) | Full Text: [PDF\(316 KB\)](#) IEEE CNF
  
- ☐ **20. H diffusion for impurity and defect passivation: a physical model for solar cell preparation**  
Sopori, B.L.; Zhang, Y.; Reedy, R.;  
Photovoltaic Specialists Conference, 2002. Conference Record of the Twenty-Ninth IEEE Photovoltaic Specialists Conference, 2002.  
19-24 May 2002 Page(s):222 - 226  
[AbstractPlus](#) | Full Text: [PDF\(399 KB\)](#) IEEE CNF
  
- ☐ **21. Damageless sputter deposition for metal gate CMOS technology**  
Takeuchi, H.; Min She; Watanabe, K.; Tsu-Jae King;  
Device Research Conference, 2003  
23-25 June 2003 Page(s):35 - 36  
[AbstractPlus](#) | Full Text: [PDF\(309 KB\)](#) IEEE CNF

[View Selected Items](#)

indexed by  
 Inspec®

[Help](#) [Contact Us](#) [Privacy & Policy](#)

© Copyright 2005 IEEE - All rights reserved.